Abstract

An SOI wafer in which a base wafer and a bond wafer respectively consisting of silicon single crystal are bonded via an oxide film, and then the bond wafer is thinned to form a silicon active layer, wherein the base wafer is formed of silicon single crystal grown by Czochralski method, and the whole surface of the base wafer is within N region outside OSF region and doesn't include a defect region detected by Cu deposition method, or the whole surface of the base wafer is within a region outside OSF region, doesn't include a defect region detected by Cu deposition method, and includes I region containing dislocation cluster due to interstitial silicon. Thereby, there is provided an SOI wafer that retains high insulating properties and has an excellent electrical reliability in device fabrication even in the case of forming an extremely thin interlevel dielectric oxide film with, for example, a thickness of 100nm or less.